

STPSC1006

600 V power Schottky silicon carbide diode

Features

- No or negligible reverse recovery
- Switching behavior independent of temperature
- Particularly suitable in PFC boost diode function

Description

The SiC diode is an ultrahigh performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide bandgap material allows the design of a Schottky diode structure with a 600 V rating. Due to the Schottky construction no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

ST SiC diodes will boost the performance of PFC operations in hard switching conditions.

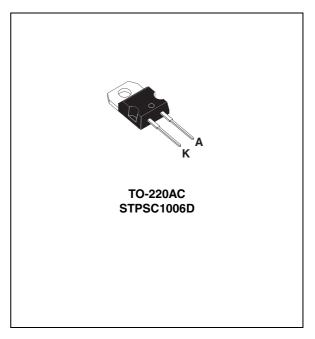


Table 1. Device summary

I _{F(AV)}	10 A
V_{RRM}	600 V
T _{j (max)}	175 °C
Q _{C (typ)}	12 nC

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1 Characteristics

Table 2. Absolute ratings (limiting values at 25 °C unless otherwise specified)

Symbol	Par	Value	Unit	
V_{RRM}	Repetitive peak reverse voltage		600	V
I _{F(RMS)}	Forward rms current		18	Α
I _{F(AV)}	Average forward current $T_c = 115$ °C, $\delta = 0.5$		10	Α
	Curae non repetitive femuera	$t_p = 10 \text{ ms sinusoidal, } T_c = 25 ^{\circ}\text{C}$	40	
I _{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms sinusoidal, } T_c = 125 ^{\circ}\text{C}$	32	Α
current	$t_p = 10 \mu s \text{ square}, T_c = 25 ^{\circ}\text{C}$	160		
I _{FRM}	Repetitive peak forward current δ = 0.1, T_C = 110 °C, T_j = 150 °C		40	Α
T _{stg}	Storage temperature range		-55 to +175	°C
Tj	Operating junction temperature	-40 to +175	°C	

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit	
R _{th(j-c)}	Junction to case	2	°C/W	

Table 4. Static electrical characteristics

Symbol	Parameter	Tests conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾	Reverse leakage	T _j = 25 °C	V - V	-	30	150	пΛ
^{'R} current	T _j = 150 °C	$V_R = V_{RRM}$	-	210	1500	μΑ	
V _F ⁽²⁾	Forward voltage drop	ge drop $T_j = 25 ^{\circ}\text{C}$ $I_F = 10 \text{A}$	-	1.4	1.7	V	
VEVALUE	i orward voitage drop	T _j = 150 °C	IF = 10 A	-	1.6	2.1	V

^{1.} $t_p = 10 \text{ ms}, \ \delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 1.2 \text{ x I}_{F(AV)} + 0.09 \text{ x I}_{F^2(RMS)}$$

Table 5. Other parameters

Symbol	Parameter	Test conditions	Тур.	Unit
Q _c	Total capacitive charge	$V_r = 400 \text{ V}, I_F = 10 \text{ A} \text{ d}I_F/\text{d}t = -200 \text{ A}/\mu\text{s}$ $T_j = 150 ^{\circ}\text{C}$	12	nC
C Total capacitance		$V_r = 0 \text{ V}, T_c = 25 \text{ °C}, F = 1 \text{ Mhz}$	650	рF
	Total Capacitatice	$V_r = 400 \text{ V}, T_c = 25 ^{\circ}\text{C}, F = 1 \text{ Mhz}$	50	ρг

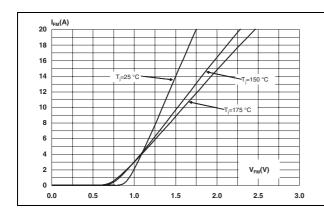
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^{2.} $t_p = 500 \ \mu s, \ \delta < 2\%$

STPSC1006 Characteristics Char

Figure 1. Forward voltage drop versus forward current (typical values)

Figure 2. Reverse leakage current versus reverse voltage applied (maximum values)



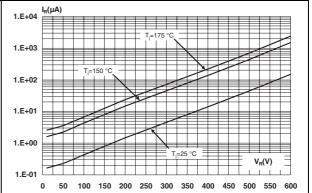
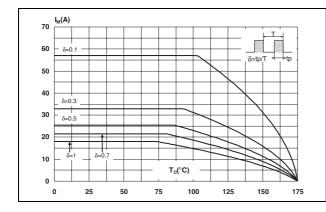


Figure 3. Peak forward current versus case temperature

Figure 4. Junction capacitance versus reverse voltage applied (typical values)



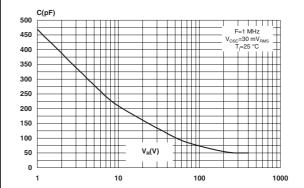


Figure 5. Relative variation of thermal impedance junction to case versus pulse duration

Z_{th(t-c)}/R_{th(t-c)}

1.0

2_{th(t-c)}/R_{th(t-c)}

1.0

0.9

0.8

0.7

0.6

0.5

0.4

0.3

0.2

0.1

Single pulse

1.E-05

1.E-04

1.E-03

1.E-02

1.E-01

1.E+00

1.E+01

Figure 6. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)

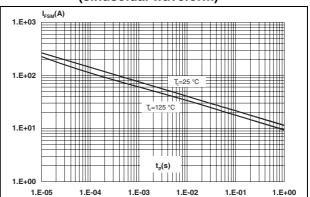
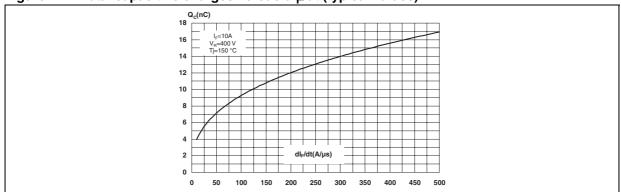


Figure 7. Total capacitive charges versus dl_F/dt (typical values)

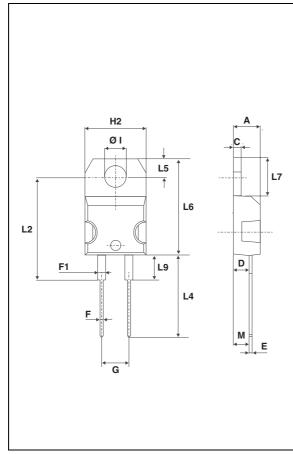


2 Package information

- Epoxy meets UL94, V0
- Cooling method: convection (C)
- Recommended torque value: 0.4 to 0.6 N⋅m

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Table 6. TO-220AC Dimensions



	Dimensions				
Ref.	Millimeters Min. Max.		Inc	hes	
			Min.	Max.	
Α	4.40	4.60	0.173	0.181	
С	1.23	1.32	0.048	0.051	
D	2.40	2.72	0.094	0.107	
Е	0.49	0.70	0.019	0.027	
F	0.61	0.88	0.024 0.034		
F1	1.14	1.70	0.044	0.066	
G	4.95	5.15	0.194 0.202		
H2	10.00	10.40	0.393	0.409	
L2	16.40 typ.		0.645 typ.		
L4	13.00	14.00 0.511 0.55		0.551	
L5	2.65	2.95	0.104	0.116	
L6	15.25	15.75	0.600	0.620	
L7	6.20	6.60	0.244	0.259	
L9	3.50	3.93	0.137	0.154	
М	2.6	typ.	0.102	2 typ.	
Diam. I	3.75	3.85	0.147 0.151		

3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPSC1006D	STPSC1006D	TO-220AC	1.86 g	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
24-Sep-2009	1	First issue

STPSC1006 www.DataSheet4U.com

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